

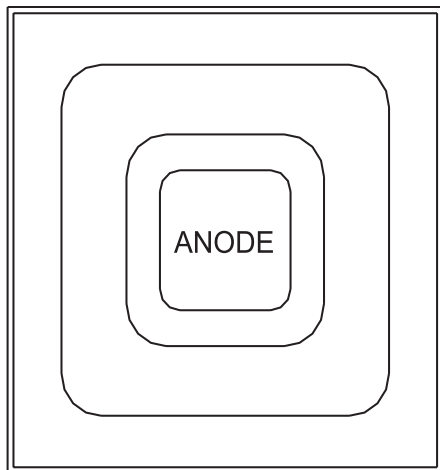
PROCESS CPD83V
Switching Diode
High Speed Switching Diode Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding pad Area	3.3 x 3.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au.As - 13,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

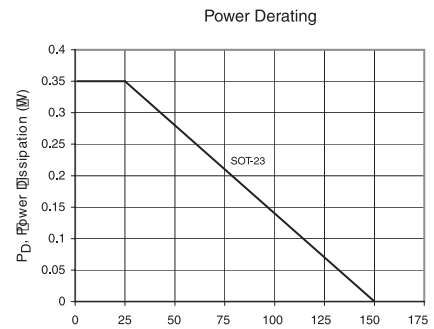
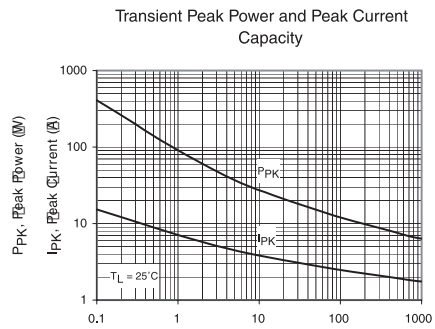
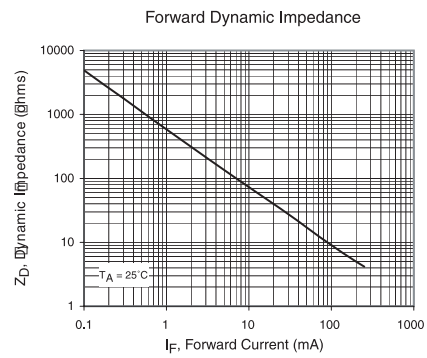
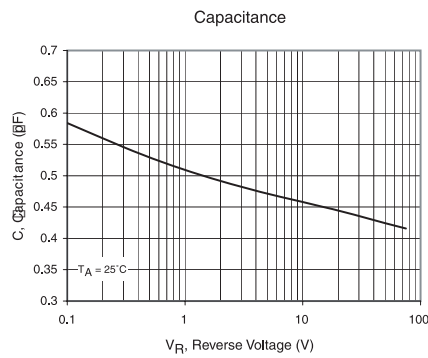
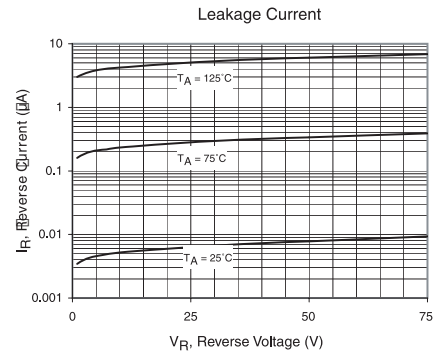
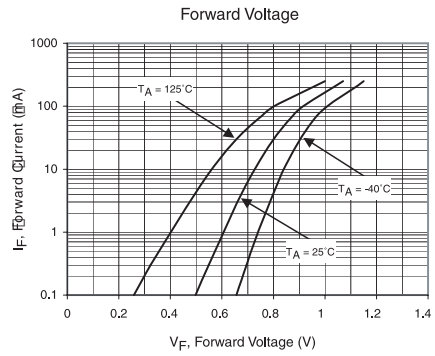
94,130

PRINCIPAL DEVICE TYPES

CMPD914
CMPD4448
1N914
1N914B
1N4148
1N4448
1N4154
1N4454
CMPD2836
CMPD2838
CMPD7000

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R1 (25- April 2005)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R1 (25- April 2005)